

# INFORMATION DISCLOSURE STATEMENT BY APPLICANT

Application No. 10/802,593  
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 First Named Inventor Chan-Yong Park  
 Art Unit 2826  
 Examiner Thomas L. Dickey  
 Attorney Docket No. GAIN3.001AUS

(Multiple sheets used when necessary)

SHEET 1 OF 1

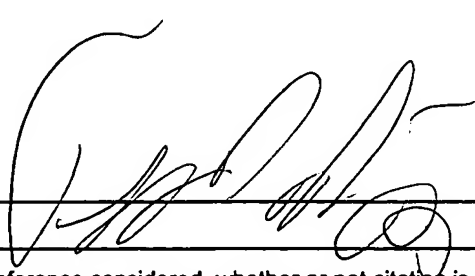
## U.S. PATENT DOCUMENTS

Examiner Initials	Cite No.	Document Number Number - Kind Code (if known) Example: 1,234,567 B1	Publication Date MM-DD-YYYY	Name of Patentee or Applicant	Pages, Columns, Lines Where Relevant Passages or Relevant Figures Appear
TV	1	US 4,326,211	04/20/1982	Eugenius T.J.M. Smeets	

## NON PATENT LITERATURE DOCUMENTS

Examiner Initials	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>1</sup>
TV	2	I. Watanabe et al., "Gain-Bandwidth Product Analysis of InAlGaAs-InAlAs Superlattice Avalanche Photodiodes" IEEE Photonics Technology Letters, Vol. 8, No. 2, pp. 269-271, 1996	
TV	3	C.Y. Park et al., "Fabrication Of InGaAs/InP Avalanche Photodiodes By Reactive Ion Etching Using CH <sub>4</sub> /H <sub>2</sub> Gases", Journal of Vacuum Science Technologies B, Vol. 13, No. 3, pp. 974-977, 1995	
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Examiner Signature	Date Considered
	4/28/05
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T<sup>1</sup> - Place a check mark in this area when an English language Translation is attached.